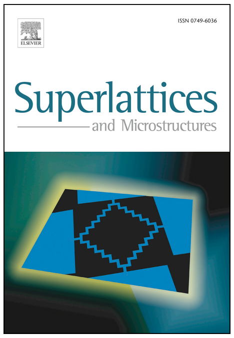

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A novel nanoscale SOI MOSFET by embedding undoped region for improving self-heating effect

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